



30V Dual N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

6 A

Features

- RDS(ON), VGS@10V, ID@6A<35mΩ
- RDS(ON), VGS@4.5V, ID@4A<40mΩ
- RDS(ON), VGS@2.5V, ID@2A<54mΩ
- Advanced Trench Process Technology
- ESD Protected 2KV HBM
- High density cell design for ultra low on-resistance
- Green molding compound as per IEC61249 Std. (Halogen Free)

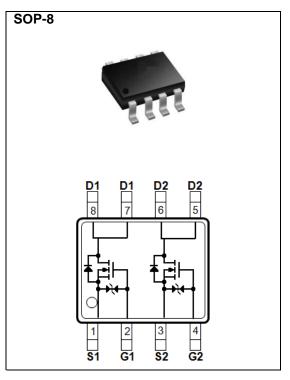
Mechanical Data

• Case: SOP-8 package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0029 ounces, 0.083 grams

Marking: L9812



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 12	V	
Continuous Drain Current	T _A =25°C		6		
	T _A =70°C	l _D	4.8	Α	
Pulsed Drain Current (Note 1)		I _{DM}	24	А	
Power Dissipation	T _A =25°C	P _D	2	W	
	T _A =70°C		1.3		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal resistance					
- Junction to Ambient, t≤10s (Note 5)		$R_{\theta JA}$	62.5	°C/W	





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.5	0.8	1.3	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =6.0A	1	30	35	mΩ
		V _{GS} =4.5V,I _D =4.0A	-	33	40	
		V _{GS} =2.5V,I _D =2.0A	-	41	54	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 12V,V _{DS} =0V	-	-	<u>+</u> 10	uA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V _{DS} =15V, I _D =6.0A, V _{GS} =4.5V ^(Note 1,2)	-	5.1	-	nC
Gate-Source Charge	Q_{gs}		-	0.8	-	
Gate-Drain Charge	Q_gd		-	1.4	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	421	-	pF
Output Capacitance	Coss		-	43	-	
Reverse Transfer Capacitance	Crss	f=200KHZ	-	35	-	
Turn-On Delay Time	td _(on)	\/ 45\/ L 4.0A	-	3.3	-	
Turn-On Rise Time	tr	$V_{DD}=15V, I_{D}=1.0A,$ $V_{GS}=10V,$ $R_{G}=3\Omega^{\text{(Note 1.2)}}$	-	24	-	ns
Turn-Off Delay Time	td _(off)		-	19	-	
Turn-Off Fall Time	tf	K _G =312	-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			_	6	6	A
Diode Forward Current	I _S		_		U	
Diode Forward Voltage	V _{SD}	I _S =6.0A, V _{GS} =0V	-	0.86	1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

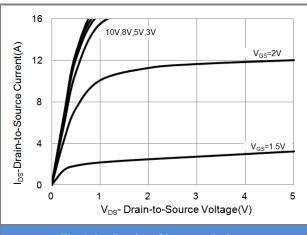


Fig.1 On-Region Characteristics

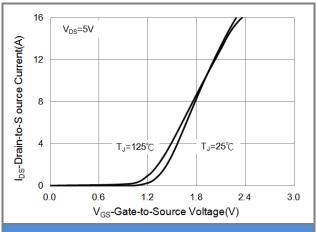


Fig.2 Transfer Characteristics

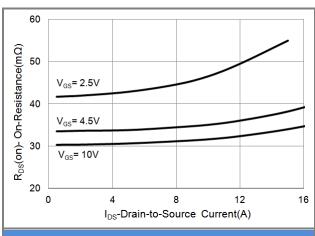


Fig.3 On-Resistance vs. Drain Current

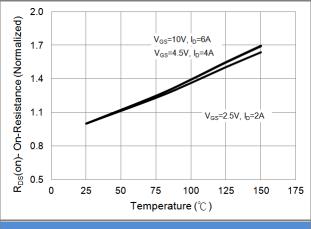


Fig.4 On-Resistance vs. Junction temperature

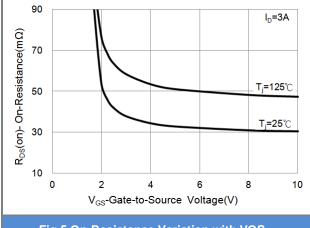


Fig.5 On-Resistance Variation with VGS.

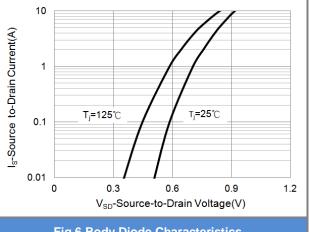


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

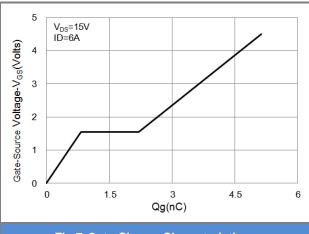


Fig.7 Gate-Charge Characteristics

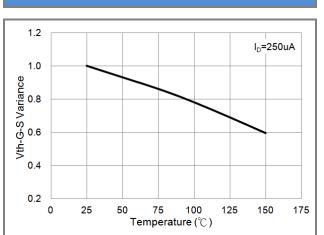


Fig.9 Threshold Voltage Variation with Temperature.

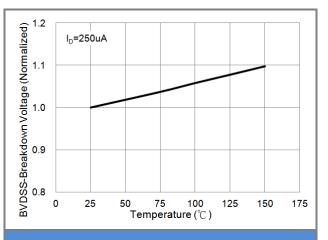


Fig.8 Breakdown Voltage Variation vs. Temperature

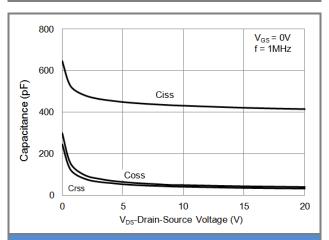


Fig.10 Capacitance vs. Drain-Source Voltage.

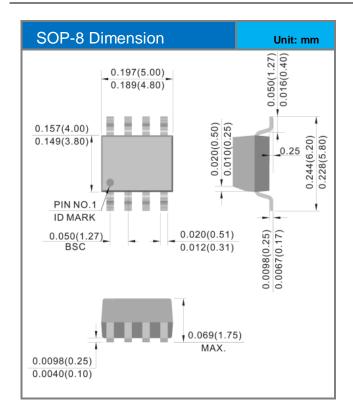


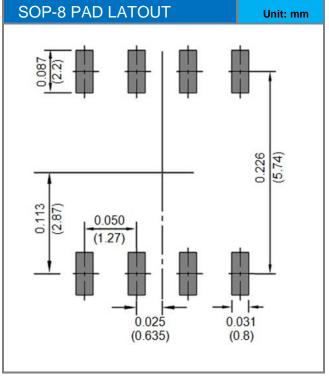


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJL9812_R2_00001	SOP-8	2.5K pcs / 13" reel	L9812	Halogen free

Packaging Information & Mounting Pad Layout









Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
 responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
 representation or warranty that such applications will be suitable for the specified use without further testing or
 modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.

单击下面可查看定价,库存,交付和生命周期等信息

>>Panjit(强茂)